

# NCE N-Channel Super Trench Power MOSFET

### Description

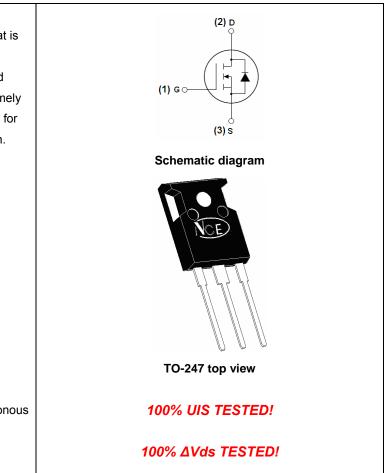
The NCEP85T35T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **General Features**

- V<sub>DS</sub> =85V,I<sub>D</sub> =350A
  R<sub>DS(ON)</sub> <1.85mΩ @ V<sub>GS</sub>=10V
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

# Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T35T	NCEP85T35T	TO-247	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	85	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι <sub>D</sub>	350	А	
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100℃)	280	А	
Pulsed Drain Current	I <sub>DM</sub>	1400	Α	
Maximum Power Dissipation	PD	520	W	
Derating factor		3.47	W/℃	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	3800	mJ	
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C	

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>ejc</sub>	0.29	°C/W	]
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# Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····		•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	85	90	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	····		•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	3	3.8	5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, I <sub>D</sub> =175A	-	1.4	1.85	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =175A	-	150	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V,	-	19500	-	PF
Output Capacitance	C <sub>oss</sub>		-	2990	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	200	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	35	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =40V,I <sub>D</sub> =100A	-	98	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>G</sub> =1.8Ω	-	110	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	45	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =40V,I <sub>D</sub> =100A,	-	324		nC
Gate-Source Charge	Q <sub>gs</sub>		-	123		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	88		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>F</sub> = 175A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	350	А
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	155		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	436		nC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board,  $t \le 10$  sec.

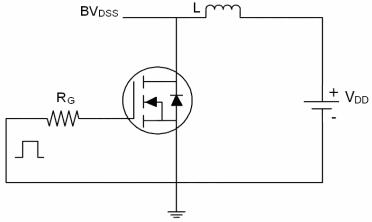
3. Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

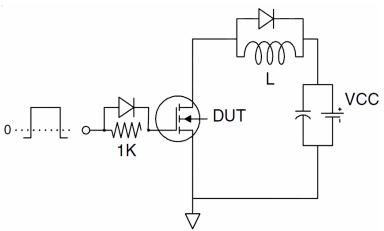
5. EAS condition : Tj=25  $^\circ\!\mathrm{C}$  ,V\_DD=42.5V,V\_G=10V,L=1mH,Rg=25\Omega



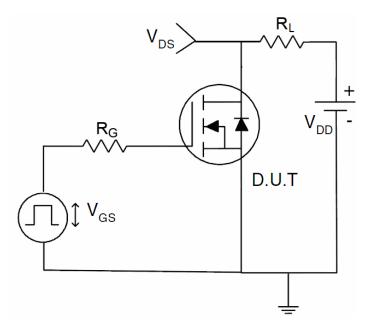
# Test Circuit 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

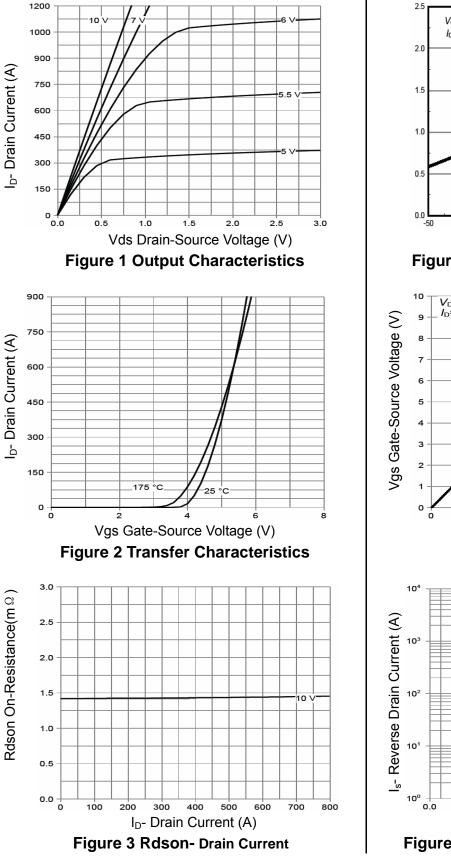


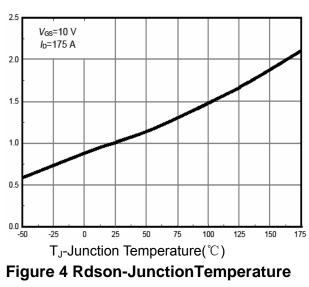
3) Switch Time Test Circuit

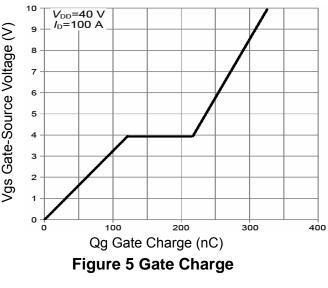


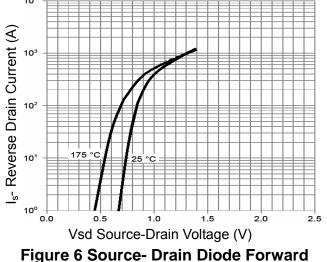


**Typical Electrical and Thermal Characteristics** 





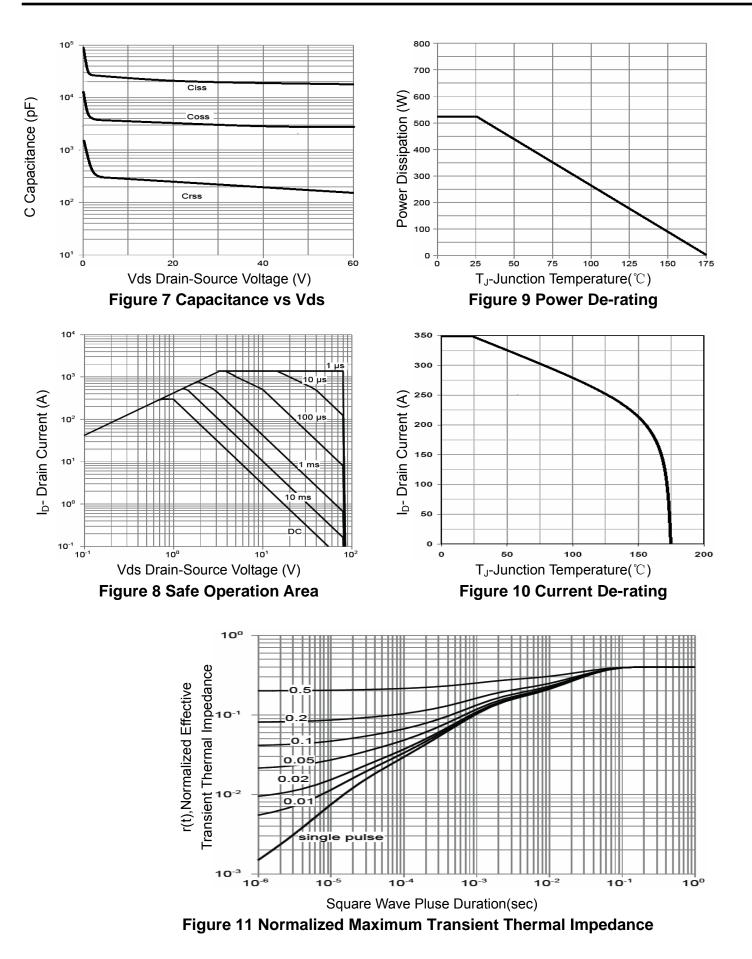




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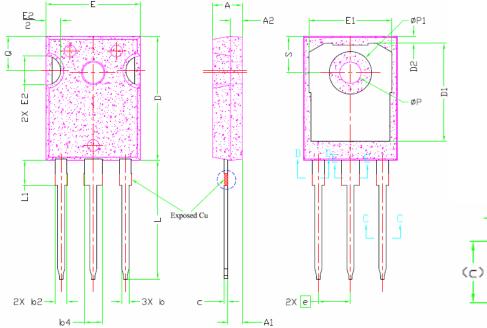


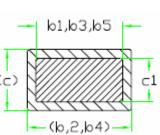
### http://www.ncepower.com





# **TO-247 Package Information**





Cumbal	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
A	4.83	5.02	5.21		
A1	2.29	2.29 2.41			
A2	1.50	2.00	2.49		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39		
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22		
b5	2.87	3.00	3.18		
С	0.55	0.60	0.69		
c1	0.55	0.60	0.65		
D	20.80	20.95	21.1		
D1	16.25	16.55	17.65		
D2	0.51	1.19	1.35		
E	15.75	15.94	16.13		
E1	13.46	14.02	14.16		
E2	4.32	4.91	5.49		
L	19.81	20.07	20.32		
L1	4.10	4.19	4.40		
Q	5.39	5.79	6.20		
ФР	3.56	3.61	3.65		
S	6.04	6.17	6.30		



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